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Multi-Level Control of Conductive Nano-Filament Evolution in HfO_2 ReRAM by Pulse-Train Operations

Supplementary Information

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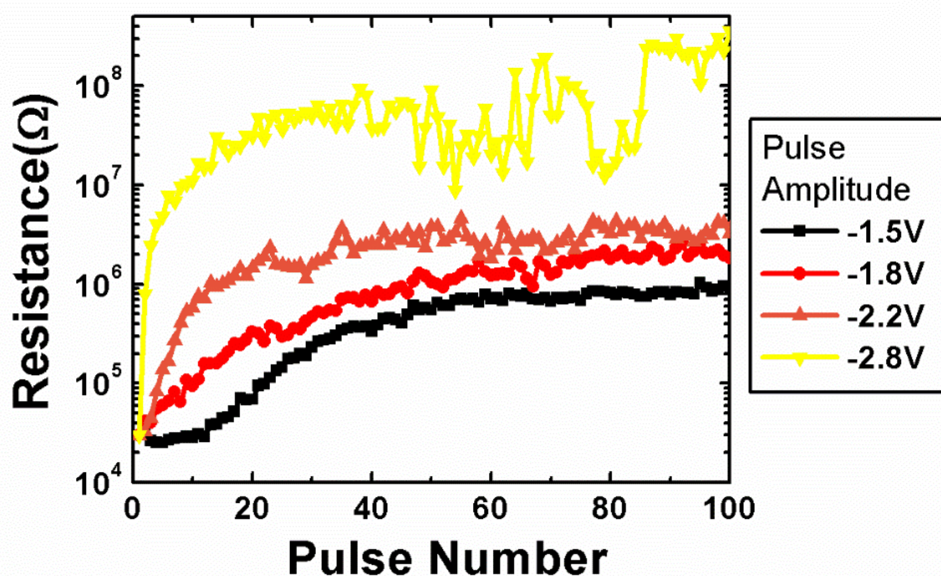

Figure S1 Resistance-change characteristics of a 1x1μm^2 TiN/HfO2/Pt device, upon the applications of 100 identical pulses with different amplitudes